

[illegible]

A cross-sectional view of a semiconductor device 10A. The device features a substrate 10 with a top surface 105. A layer 50 is formed on the top surface 105. A patterned layer 52 is formed on top of layer 50, with openings 9. A layer 20 is formed on top of layer 52. A layer 21 is formed on top of layer 20. A layer 53 is formed on top of layer 21. A layer 201 is formed on top of layer 53. A layer 202 is formed on top of layer 201. The device is shown in a cross-section between points H and H'.

FIG. 3

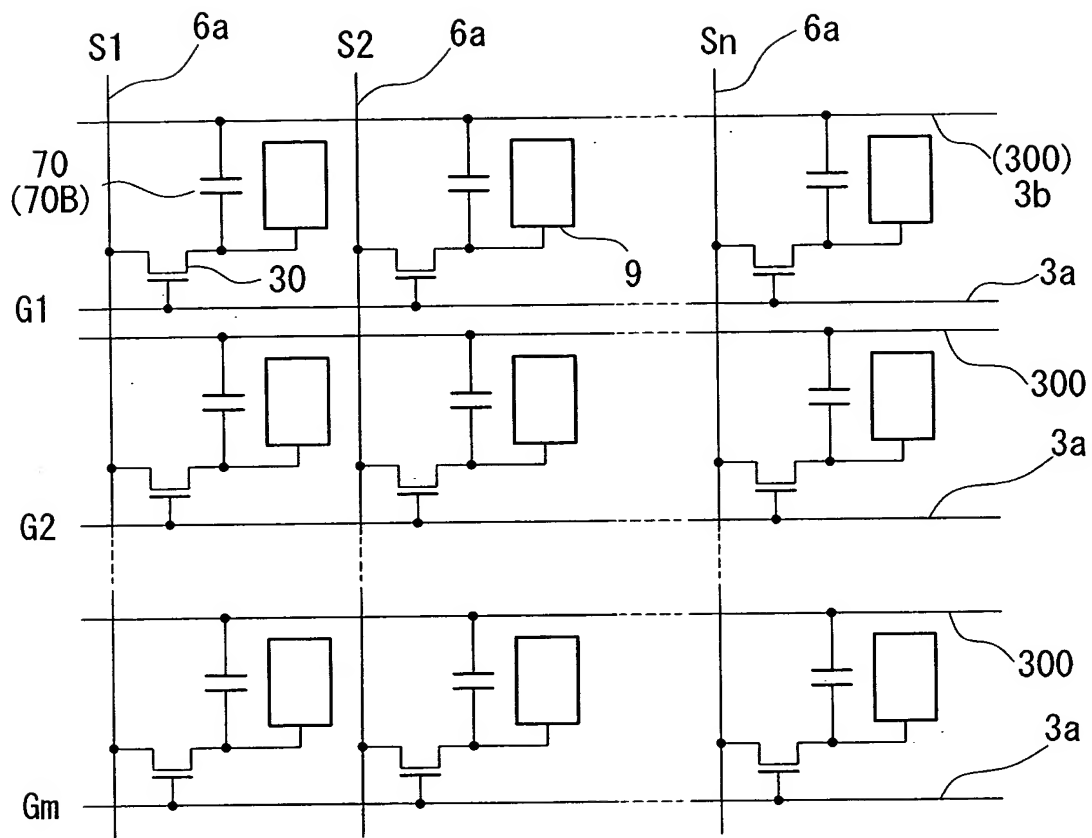


FIG. 4

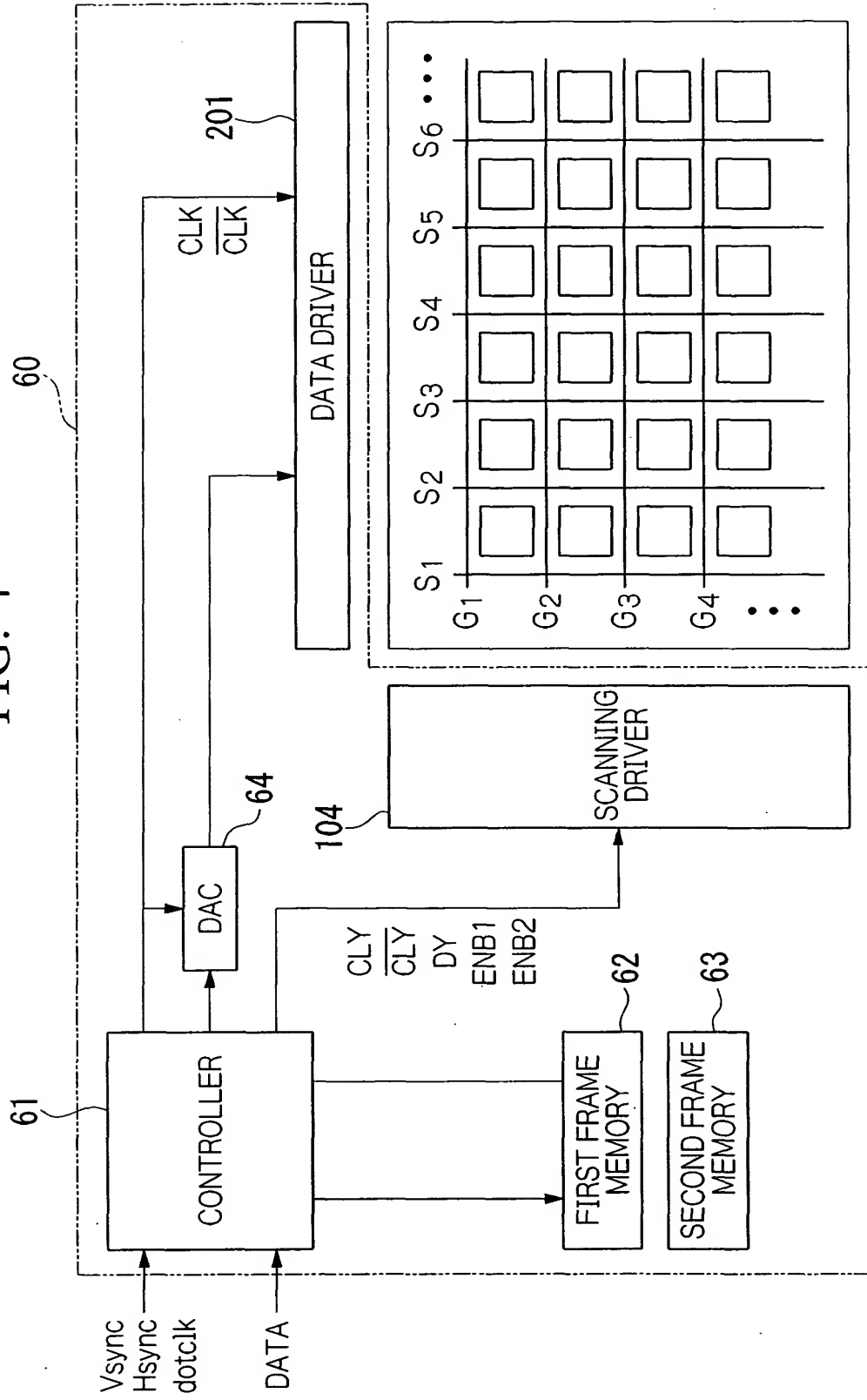


FIG. 5

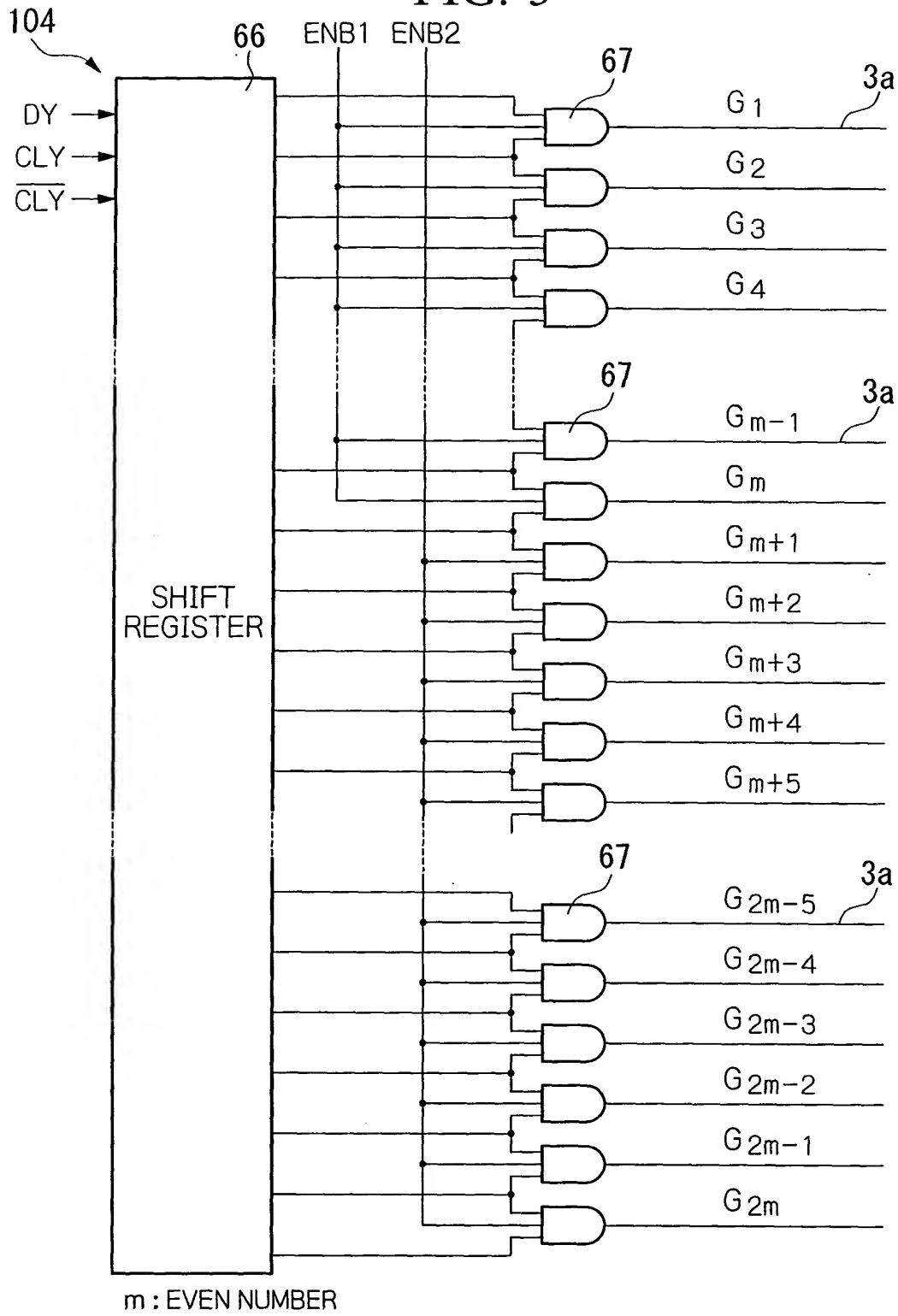


FIG. 6

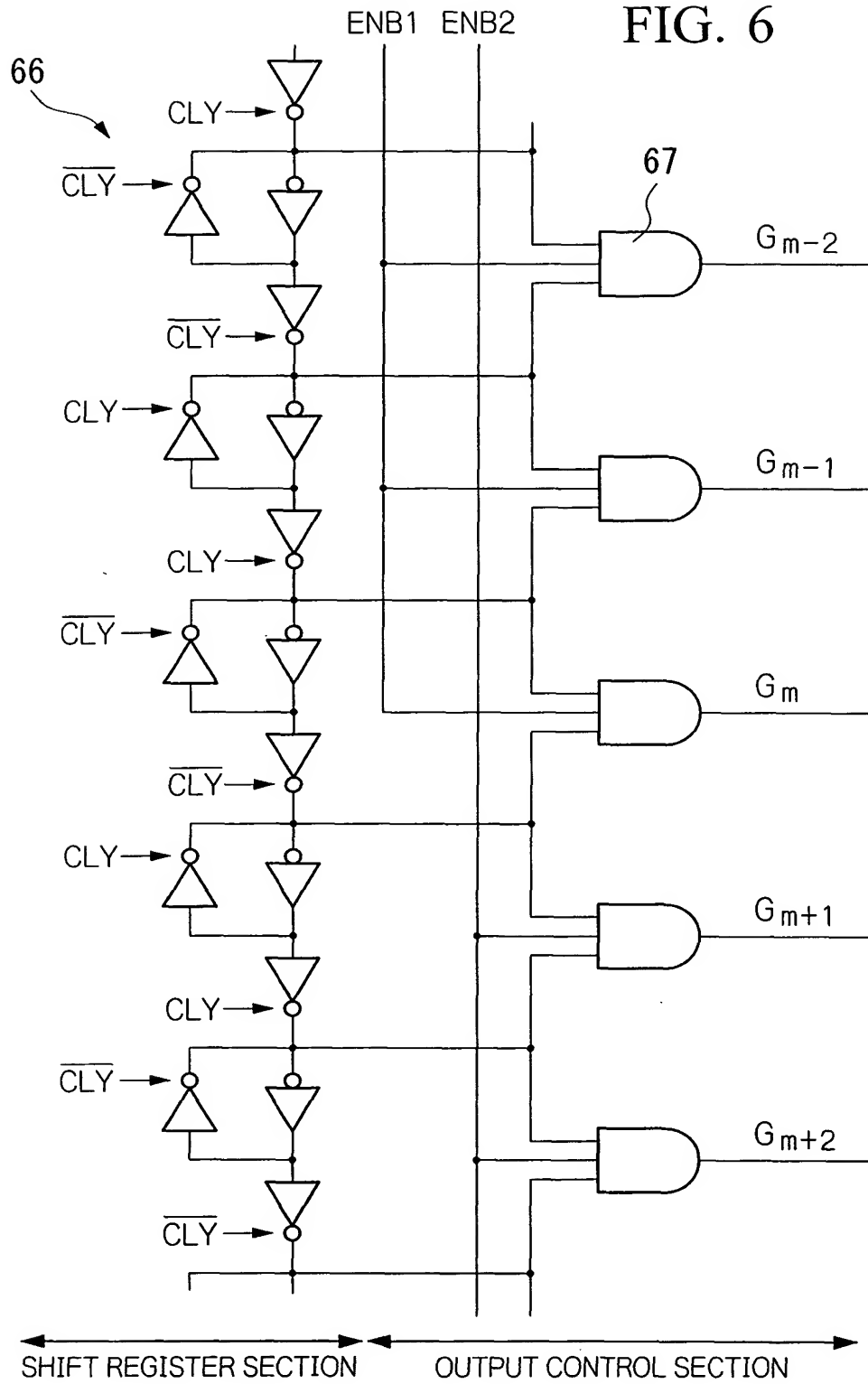


FIG. 7

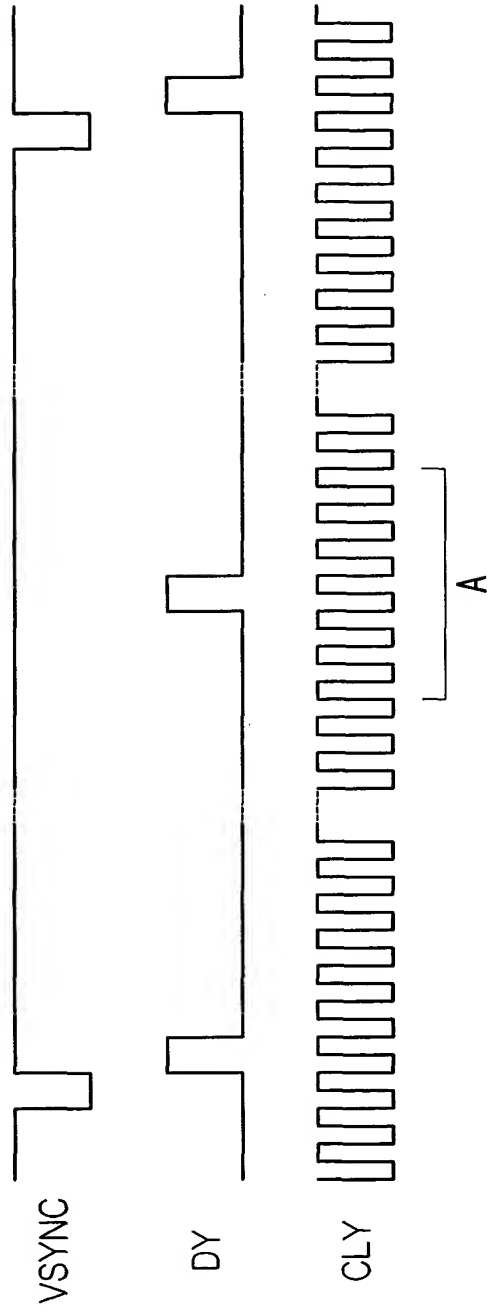


FIG. 8

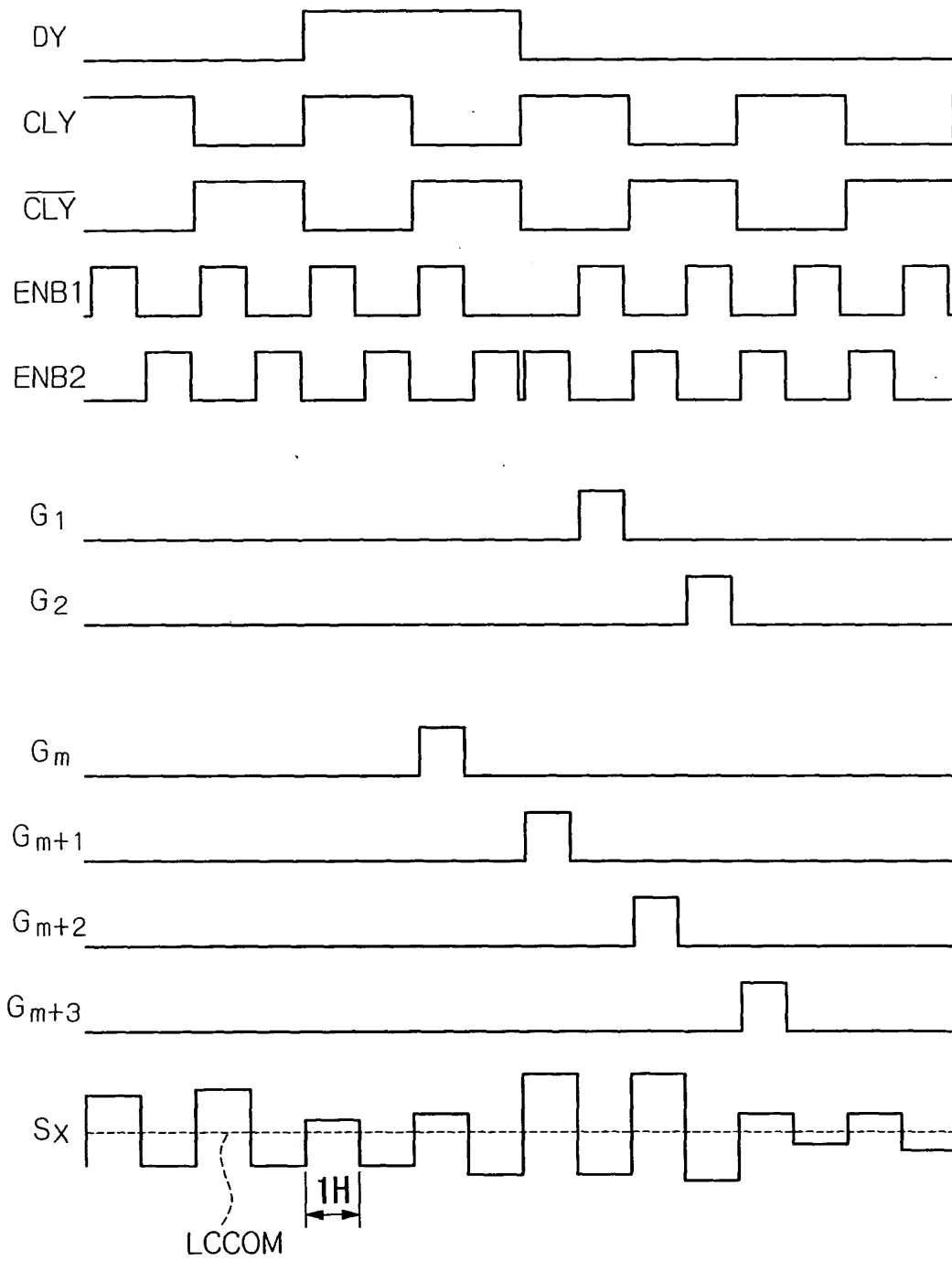


FIG. 9

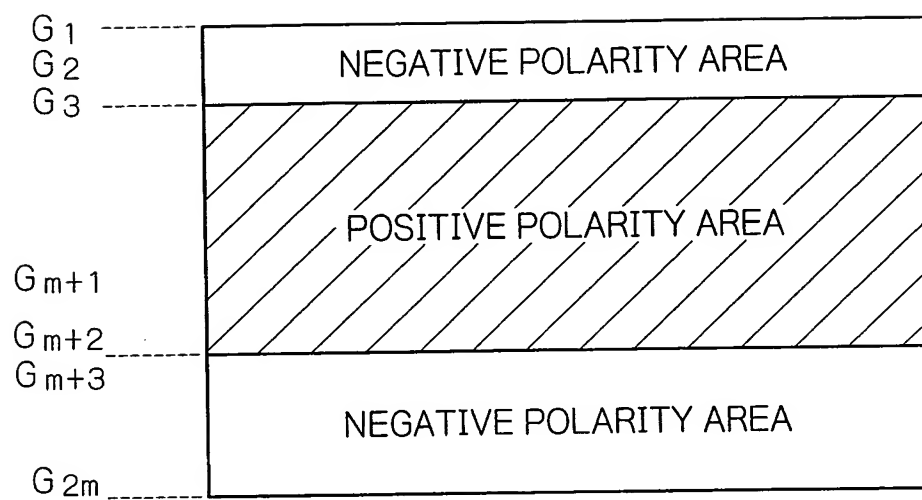




FIG. 10

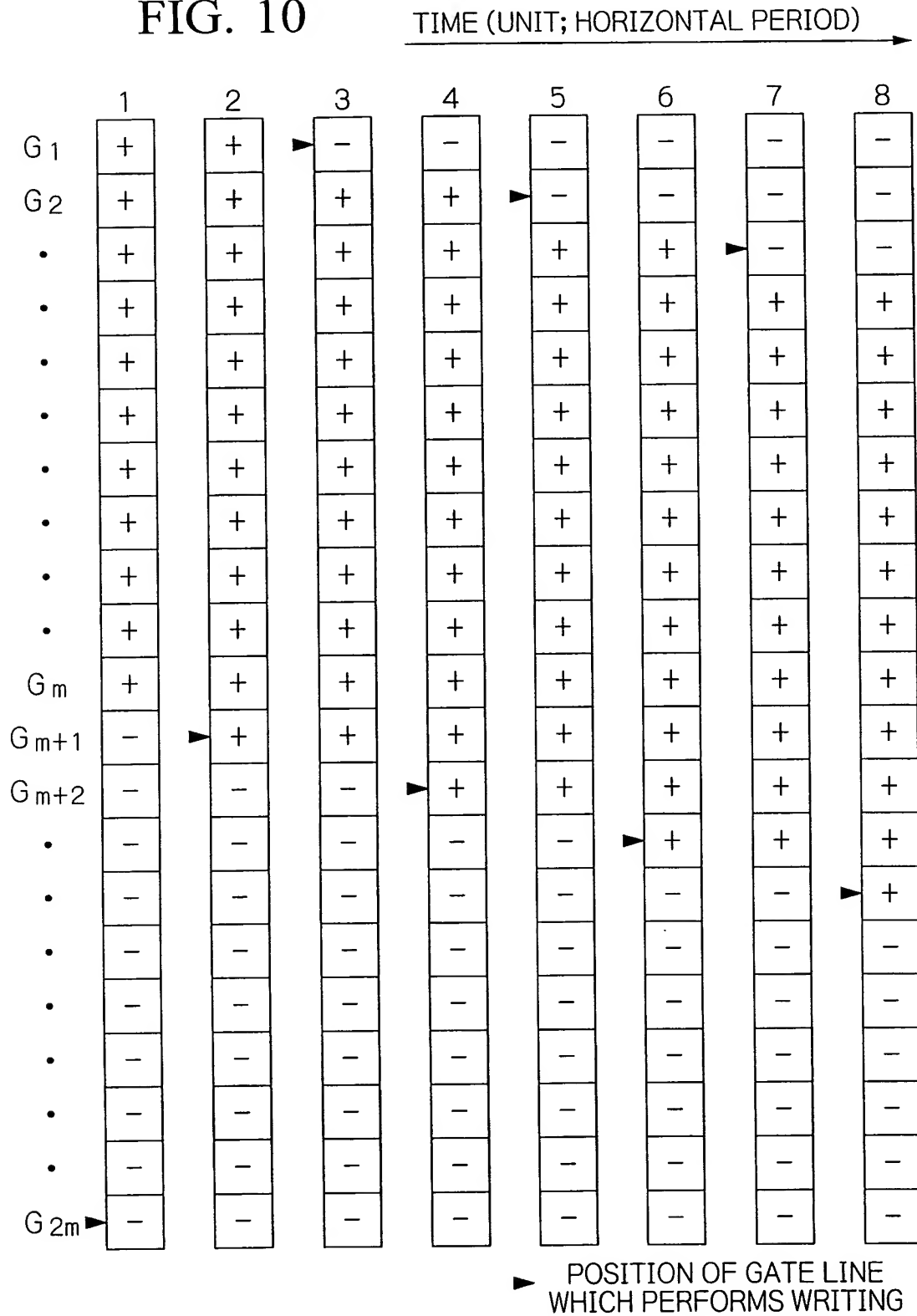


FIG. 11

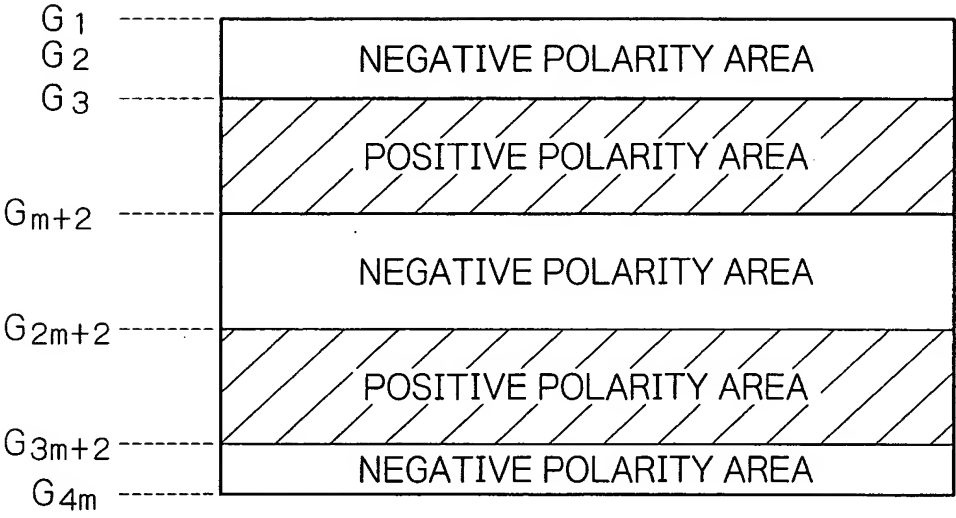


FIG. 12

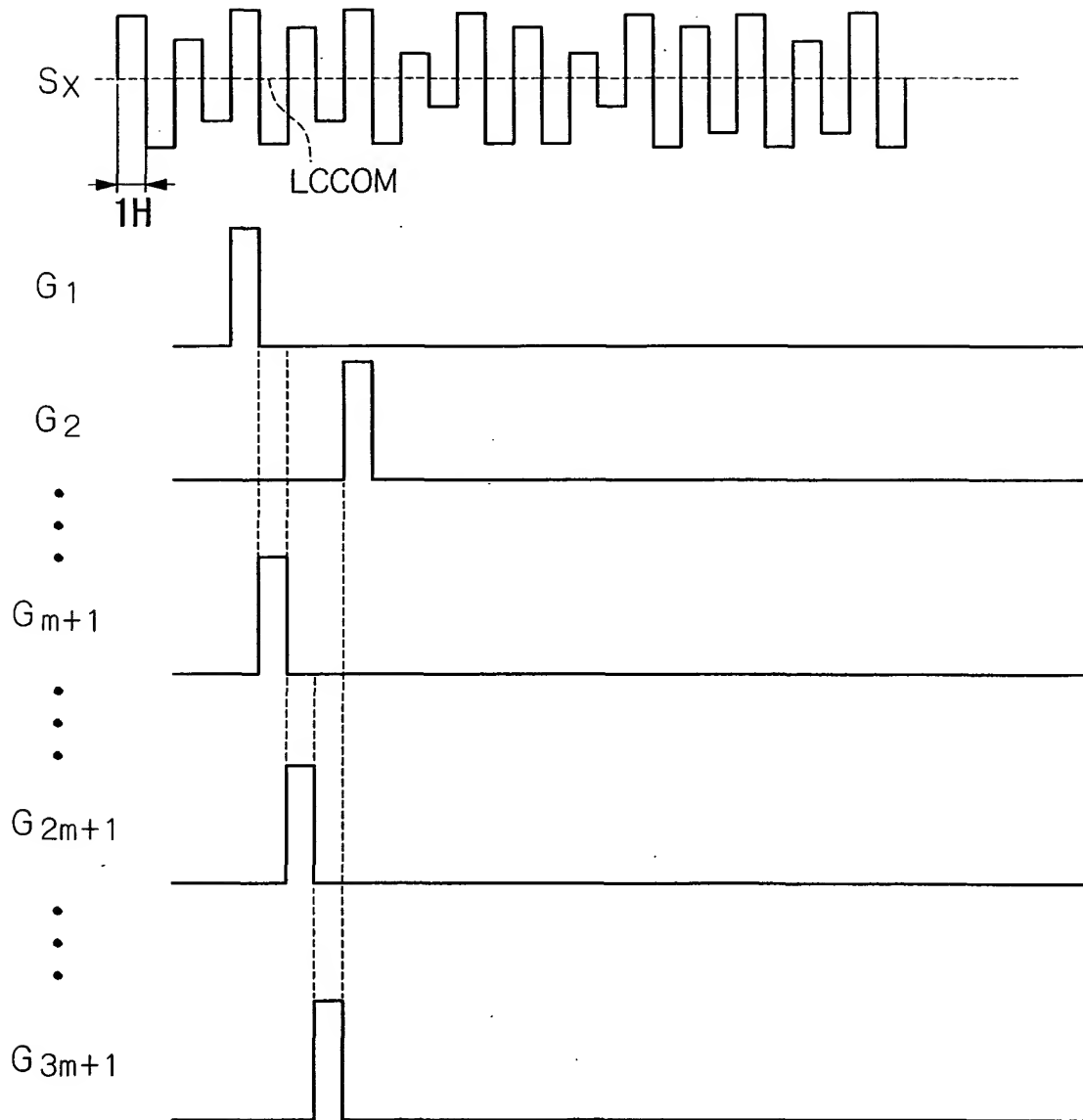


FIG. 13

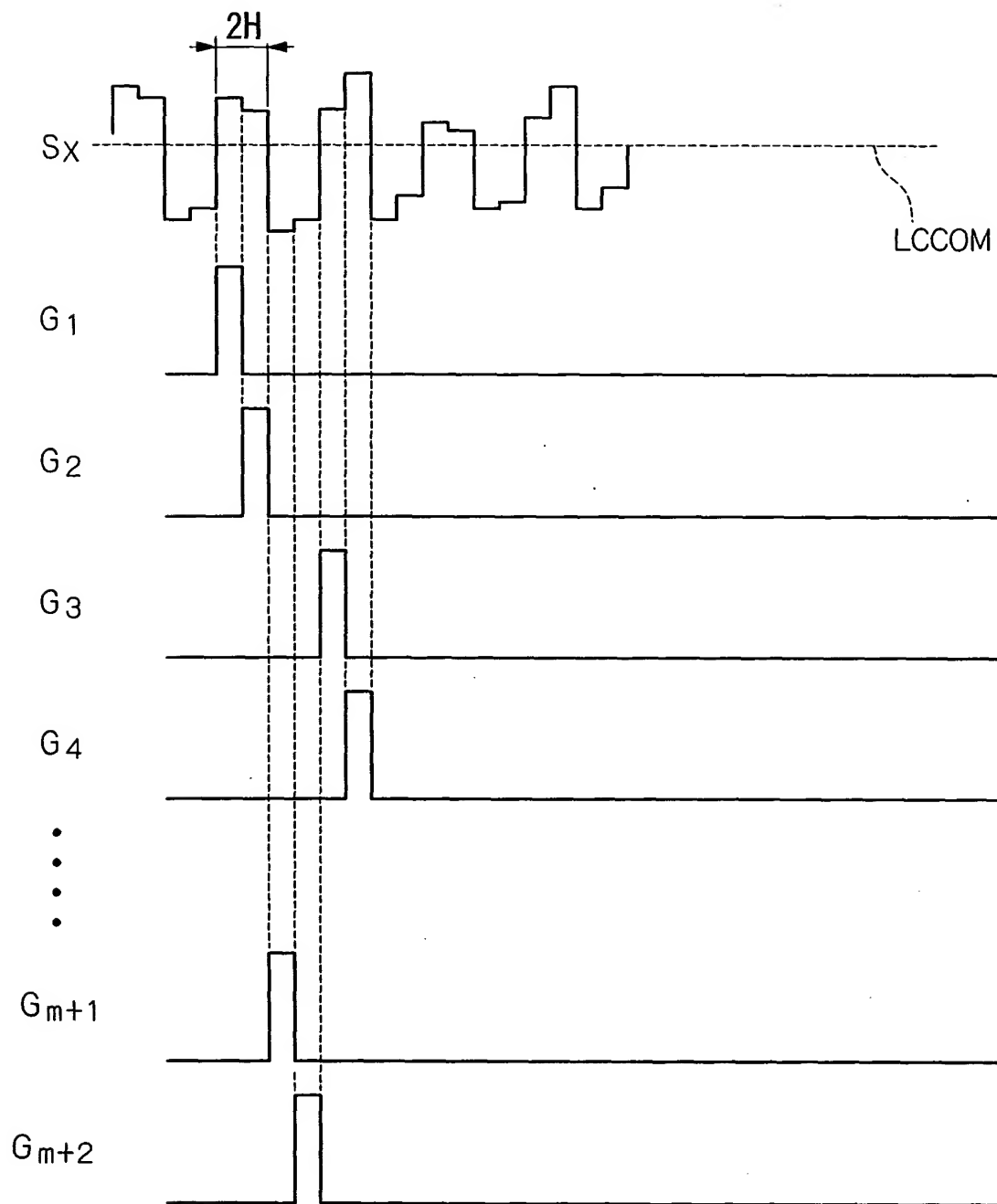


FIG. 14

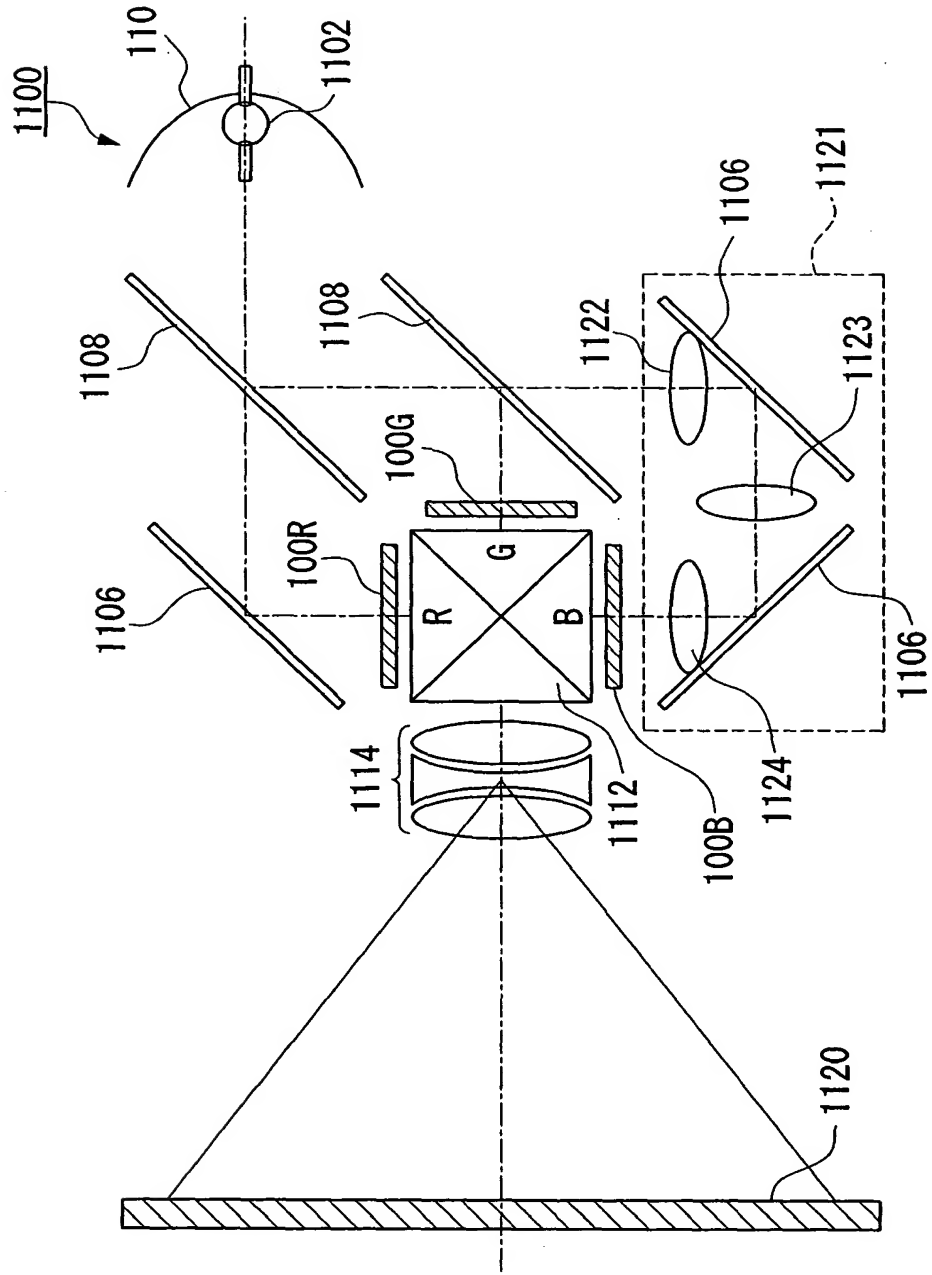


FIG. 15

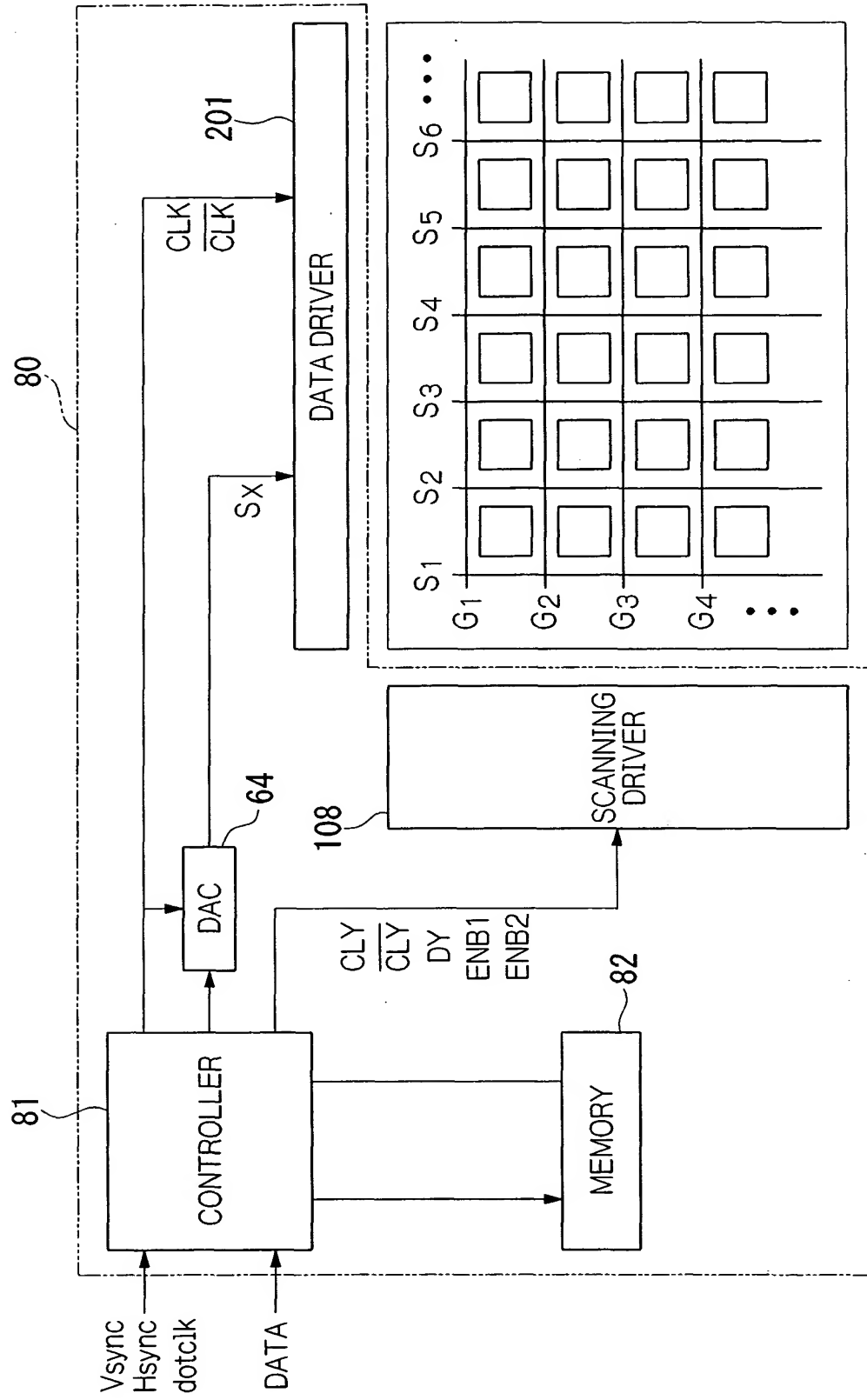


FIG. 16

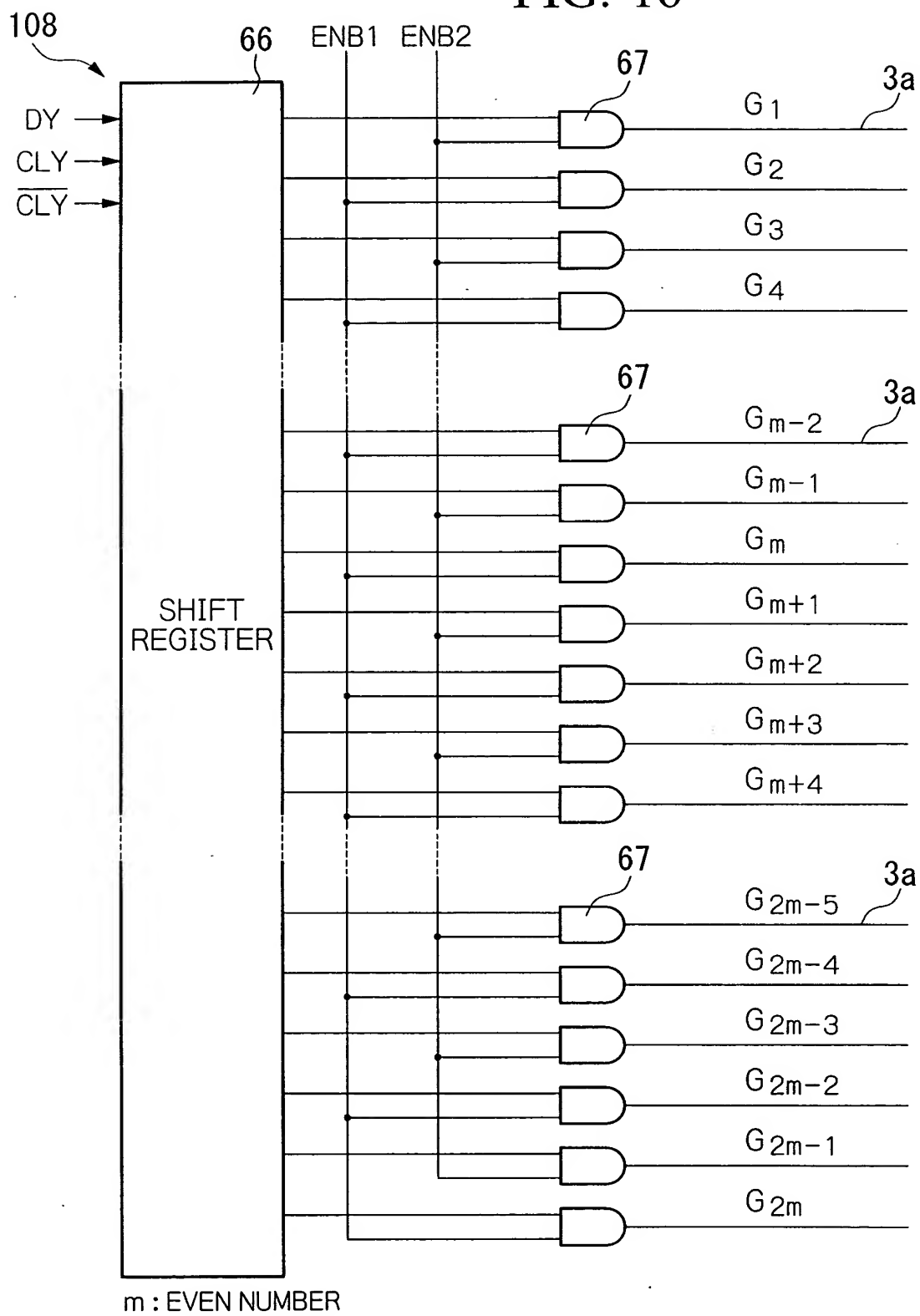


FIG. 17

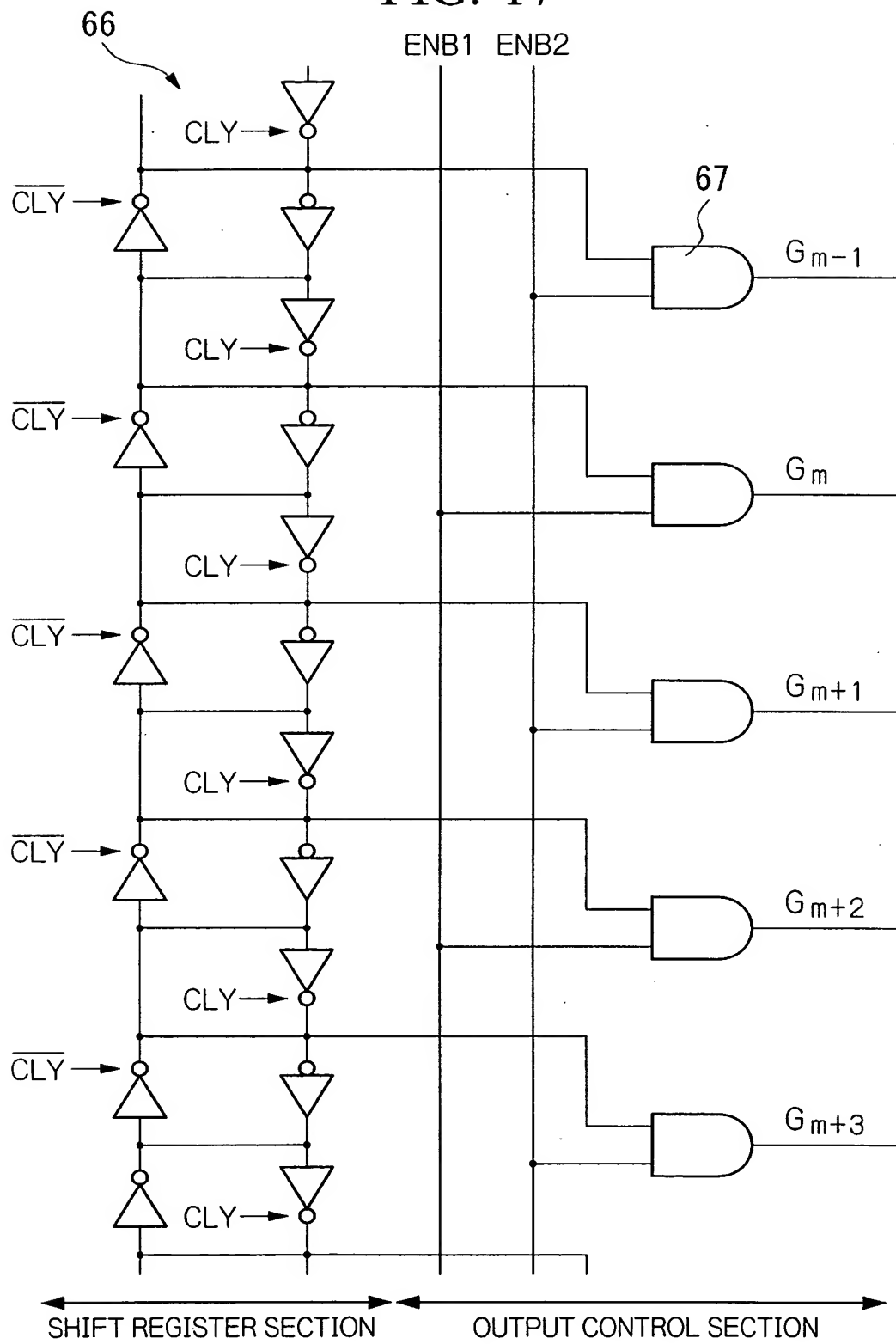




FIG. 18

